ABSTRACT

The present invention provides a single wafer processor structured such that similar immersion treatment to the conventional immersion treatment can be performed in the spin treatment, that a consumption of the chemical solutions can be reduced in the chemical solution treatment per wafer, that energy saving can be realized by using reaction heat of the chemical solutions to eliminate a necessity of a heating heater, that a problem of deterioration of the chemical solutions can be eliminated since the blending of the chemical solutions is implemented on the rotary disk part and the chemical solutions are used immediately thereafter, and that the maximum effective point of the chemical solutions can be utilized. The processor of the present invention includes: a rotary disk (12) having medium flow passages on an upper surface thereof; a plurality of wafer receiving parts (18) provided on the upper surface of the rotary disk; an annular dam member (48) located outward of an outer circumferential edge of a wafer (w) mounted on the wafer receiving parts and provided so that an upper edge of the annular dam member can be located at an upper level than an upper surface of the wafer thus mounted; and nozzle means (60a-d), provided above the wafer mounted on the wafer receiving parts, for supplying a chemical solution and rinse water.